

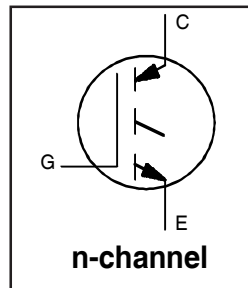
# IRG4PH50S-EPbF

INSULATED GATE BIPOLAR TRANSISTOR

Standard Speed IGBT

## Features

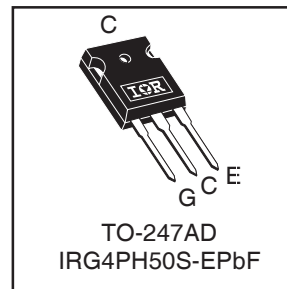
- Standard: Optimized for minimum saturation voltage and low operating frequencies (< 1kHz)
- Generation 4 IGBT design provides tighter parameter distribution and higher efficiency than Generation 3
- Industry standard TO-247AC package
- Lead-Free



$V_{CES} = 1200V$
$V_{CE(on)} \text{ typ.} = 1.47V$
@ $V_{GE} = 15V, I_C = 33A$

## Benefits

- Generation 4 IGBT's offer highest efficiency available
- IGBT's optimized for specified application conditions
- Designed to be a "drop-in" replacement for equivalent industry-standard Generation 3 IR IGBT's



## Absolute Maximum Ratings

	Parameter	Max.	Units
$V_{CES}$	Collector-to-Emitter Voltage	1200	V
$I_C @ T_C = 25^\circ C$	Continuous Collector Current	57	A
$I_C @ T_C = 100^\circ C$	Continuous Collector Current	33	
$I_{CM}$	Pulsed Collector Current <sup>①</sup>	114	
$I_{LM}$	Clamped Inductive Load Current <sup>②</sup>	114	
$V_{GE}$	Gate-to-Emitter Voltage	$\pm 20$	V
	Transient Gate-to-Emitter Voltage	$\pm 30$	
$E_{ARV}$	Reverse Voltage Avalanche Energy <sup>③</sup>	270	mJ
$P_D @ T_C = 25^\circ$	Maximum Power Dissipation	200	W
$P_D @ T_C = 100^\circ$	Maximum Power Dissipation	80	
$T_J$	Operating Junction and	-55 to + 150	$^\circ C$
$T_{STG}$	Storage Temperature Range		
	Soldering Temperature, for 10 sec.	300 (0.063 in. (1.6mm) from case)	
	Mounting Torque, 6-32 or M3 Screw.	10 lbf·in (1.1 N·m)	

## Thermal Resistance

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	—	0.64	$^\circ C/W$
$R_{\theta CS}$	Case-to-Sink, Flat, Greased Surface	—	0.24	—	
$R_{\theta JA}$	Junction-to-Ambient, typical socket mount	—	—	40	
Wt	Weight	—	6.0(0.21)	—	g (oz)

## Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

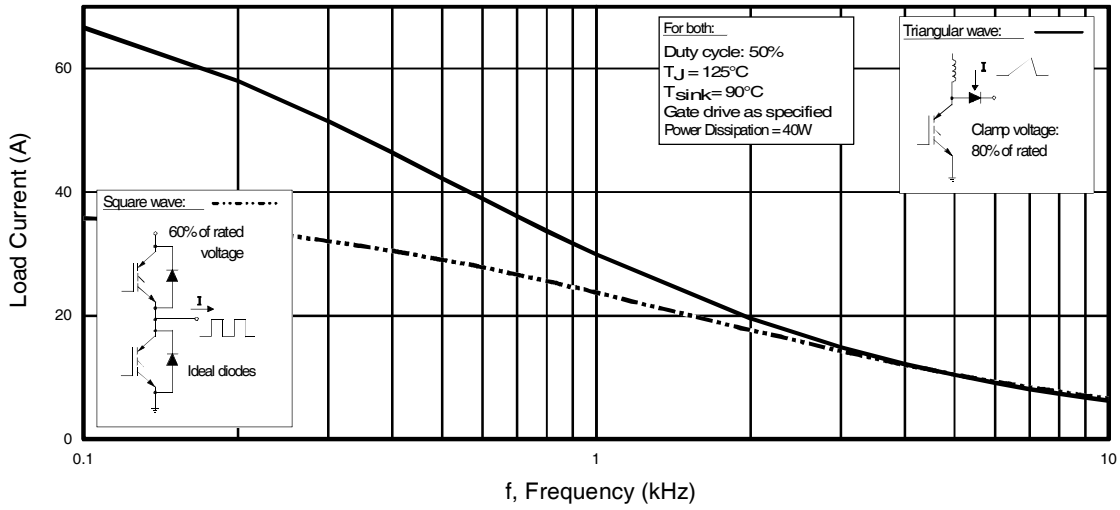
	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)CES}$	Collector-to-Emitter Breakdown Voltage	1200	—	—	V	$V_{GE} = 0V, I_C = 250\mu A$
$V_{(BR)ECS}$	Emitter-to-Collector Breakdown Voltage ④	18	—	—	V	$V_{GE} = 0V, I_C = 1.0 A$
$\Delta V_{(BR)CES}/\Delta T_J$	Temperature Coeff. of Breakdown Voltage	—	1.22	—	V/°C	$V_{GE} = 0V, I_C = 2.0 mA$
$V_{CE(ON)}$	Collector-to-Emitter Saturation Voltage	—	1.47	1.7	V	$I_C = 33A, V_{GE} = 15V$ See Fig.2, 5
		—	1.75	—		
		—	1.55	—		
$V_{GE(th)}$	Gate Threshold Voltage	3.0	—	6.0		$V_{CE} = V_{GE}, I_C = 250\mu A$
$DV_{GE(th)}/DT_J$	Temperature Coeff. of Threshold Voltage	—	-11	—	mV/°C	$V_{CE} = V_{GE}, I_C = 250\mu A$
$g_{fe}$	Forward Transconductance ⑤	27	40	—	S	$V_{CE} = 100V, I_C = 33A$
$I_{CES}$	Zero Gate Voltage Collector Current	—	—	250	$\mu A$	$V_{GE} = 0V, V_{CE} = 1200V$
		—	—	2.0		$V_{GE} = 0V, V_{CE} = 10V, T_J = 25^\circ C$
		—	—	1000		$V_{GE} = 0V, V_{CE} = 1200V, T_J = 150^\circ C$
$I_{GES}$	Gate-to-Emitter Leakage Current	—	—	$\pm 100$	nA	$V_{GE} = \pm 20V$

## Switching Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

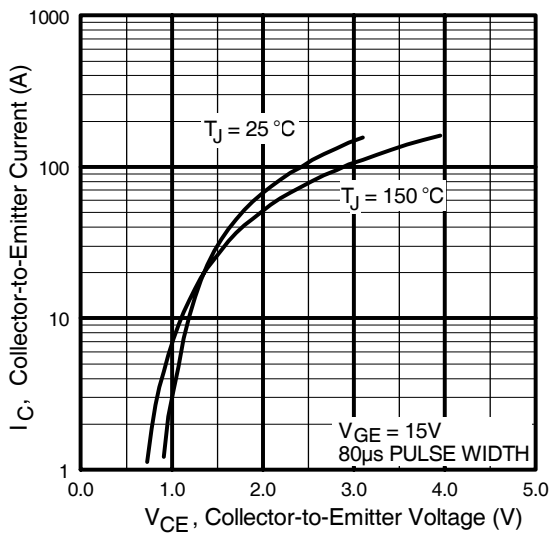
	Parameter	Min.	Typ.	Max.	Units	Conditions
$Q_g$	Total Gate Charge (turn-on)	—	167	251	nC	$I_C = 33A$ $V_{CC} = 400V$ See Fig. 8 $V_{GE} = 15V$
$Q_{ge}$	Gate - Emitter Charge (turn-on)	—	25	38		
$Q_{gc}$	Gate - Collector Charge (turn-on)	—	55	83		
$t_{d(on)}$	Turn-On Delay Time	—	32	—	ns	$T_J = 25^\circ C$ $I_C = 33A, V_{CC} = 960V$ $V_{GE} = 15V, R_G = 5.0\Omega$ Energy losses include "tail" See Fig. 9, 10, 14
$t_r$	Rise Time	—	29	—		
$t_{d(off)}$	Turn-Off Delay Time	—	845	1268		
$t_f$	Fall Time	—	425	638		
$E_{on}$	Turn-On Switching Loss	—	1.80	—	mJ	See Fig. 9, 10, 14
$E_{off}$	Turn-Off Switching Loss	—	19.6	—		
$E_{ts}$	Total Switching Loss	—	21.4	44		
$t_{d(on)}$	Turn-On Delay Time	—	32	—	ns	$T_J = 150^\circ C,$ $I_C = 33A, V_{CC} = 960V$ $V_{GE} = 15V, R_G = 5.0\Omega$ Energy losses include "tail" See Fig. 10,11,14
$t_r$	Rise Time	—	30	—		
$t_{d(off)}$	Turn-Off Delay Time	—	1170	—		
$t_f$	Fall Time	—	1000	—		
$E_{ts}$	Total Switching Loss	—	37	—	mJ	See Fig. 10,11,14
$L_E$	Internal Emitter Inductance	—	13	—	nH	Measured 5mm from package
$C_{ies}$	Input Capacitance	—	3600	—	pF	$V_{GE} = 0V$ $V_{CC} = 30V$ See Fig. 7 $f = 1.0MHz$
$C_{oes}$	Output Capacitance	—	160	—		
$C_{res}$	Reverse Transfer Capacitance	—	30	—		

### Notes:

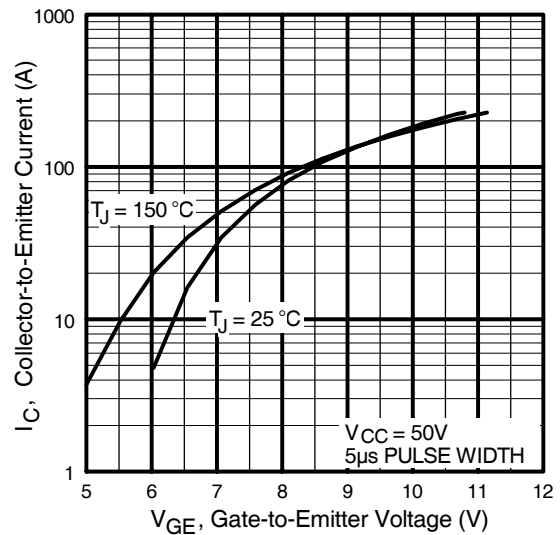
- ① Repetitive rating;  $V_{GE} = 20V$ , pulse width limited by max. junction temperature. ( See fig. 13b )
- ②  $V_{CC} = 80\%(V_{CES}), V_{GE} = 20V, L = 10\mu H, R_G = 5.0\Omega,$  (See fig. 13a)
- ③ Repetitive rating; pulse width limited by maximum junction temperature.
- ④ Pulse width  $\leq 80\mu s$ ; duty factor  $\leq 0.1\%$ .
- ⑤ Pulse width  $5.0\mu s$ , single shot.



**Fig. 1 - Typical Load Current vs. Frequency**  
(Load Current =  $I_{\text{RMS}}$  of fundamental)



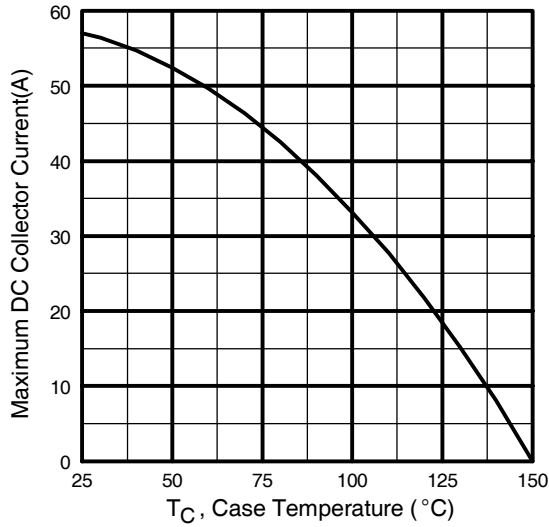
**Fig. 2 - Typical Output Characteristics**



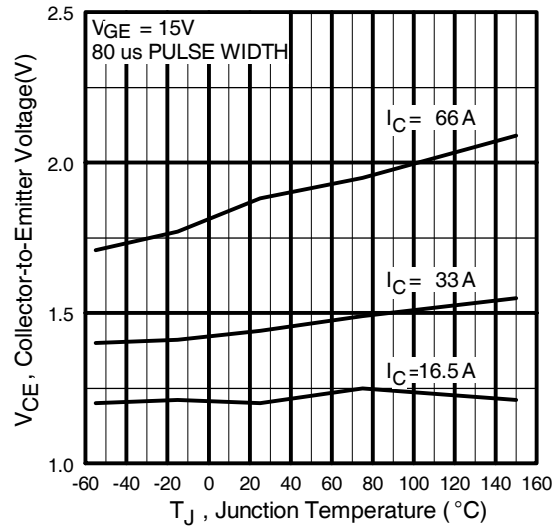
**Fig. 3 - Typical Transfer Characteristics**

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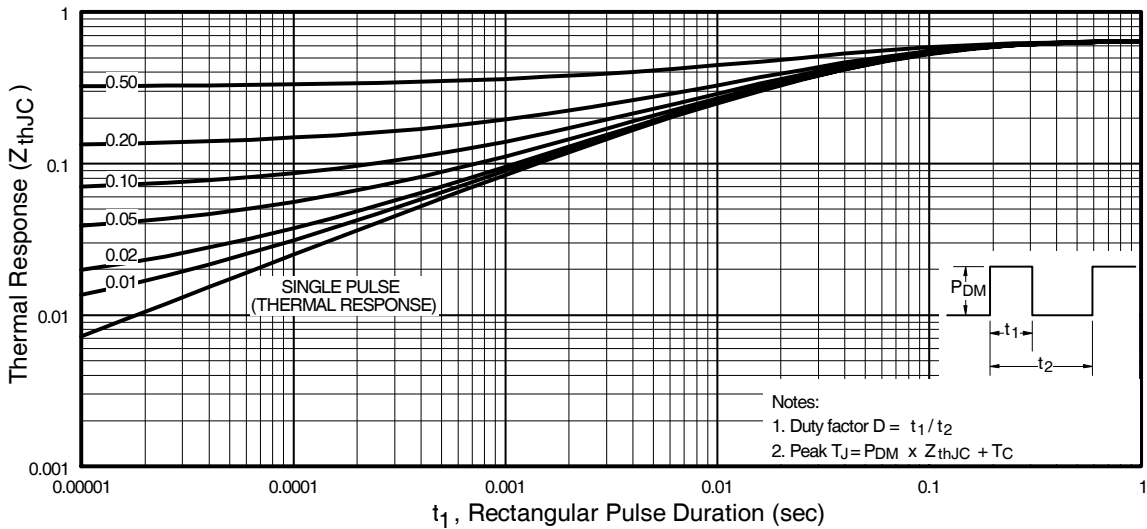
International  
**IR** Rectifier



**Fig. 4** - Maximum Collector Current vs. Case Temperature

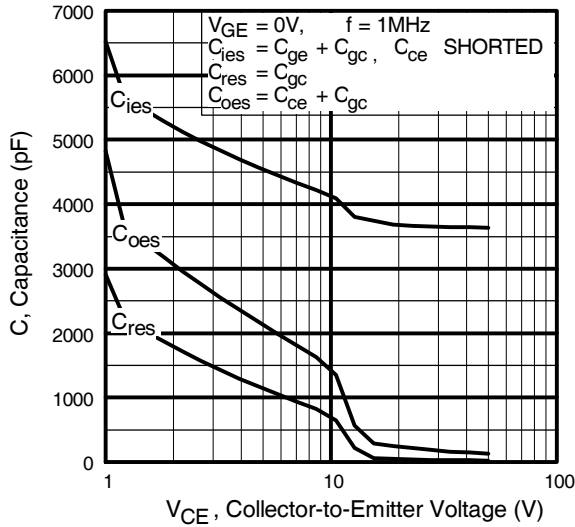


**Fig. 5** - Typical Collector-to-Emitter Voltage vs. Junction Temperature

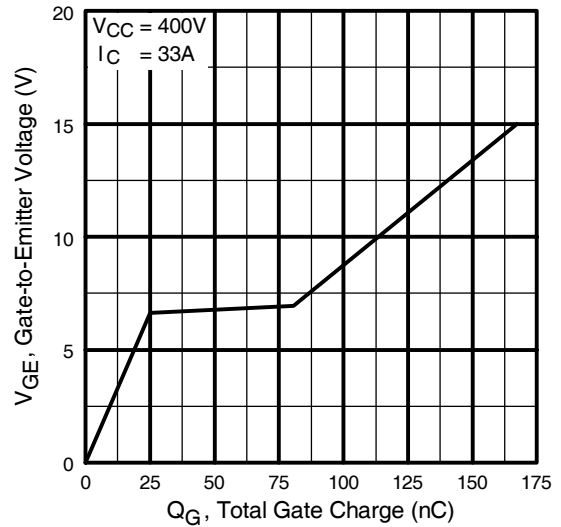


**Fig. 6** - Maximum Effective Transient Thermal Impedance, Junction-to-Case

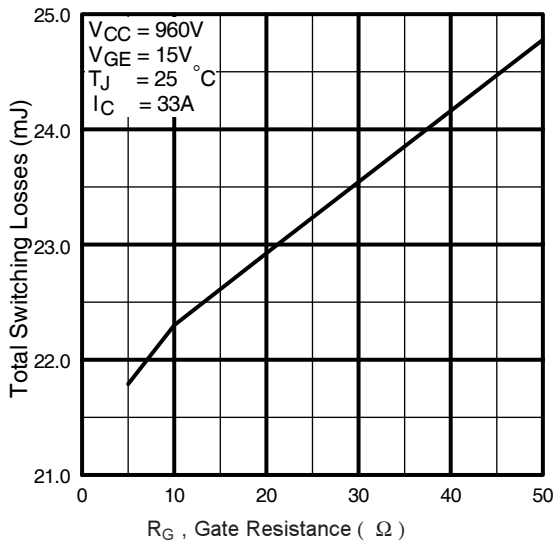
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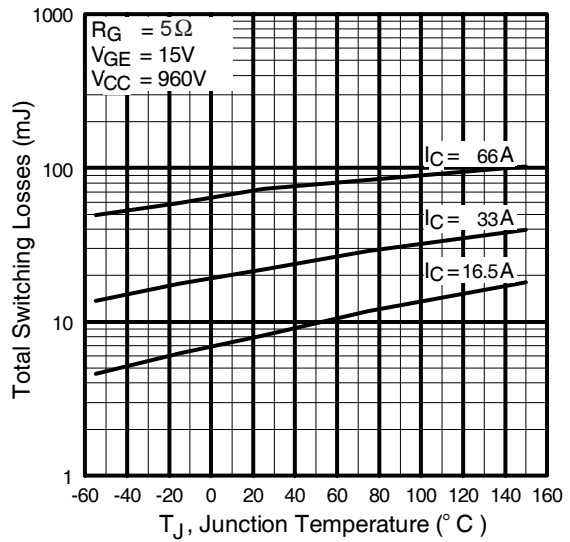
**Fig. 7** - Typical Capacitance vs. Collector-to-Emitter Voltage



**Fig. 8** - Typical Gate Charge vs. Gate-to-Emitter Voltage



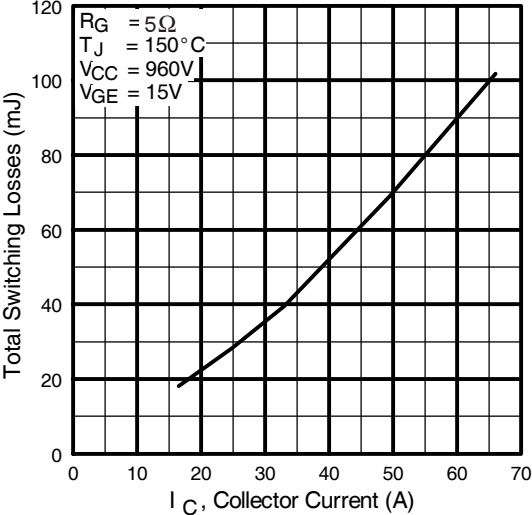
**Fig. 9** - Typical Switching Losses vs. Gate Resistance



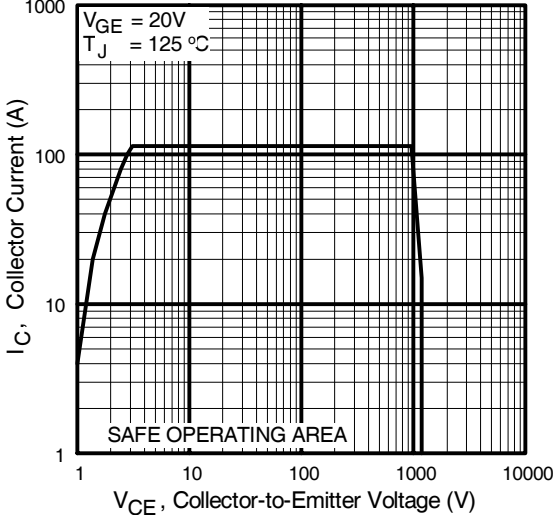
**Fig. 10** - Typical Switching Losses vs. Junction Temperature

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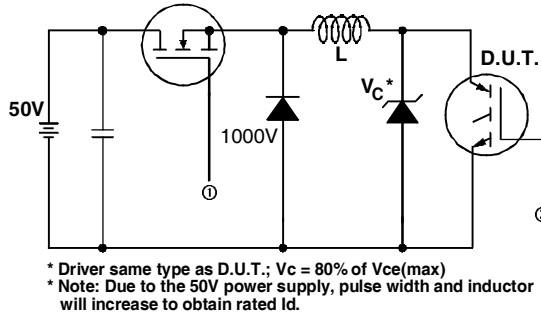
International  
**IR** Rectifier



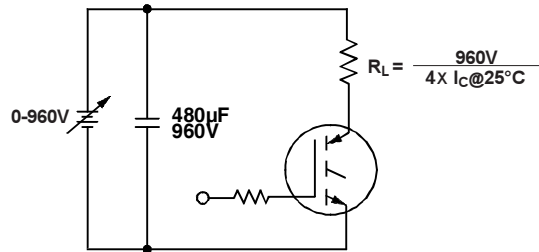
**Fig. 11** - Typical Switching Losses vs. Collector-to-Emitter Current



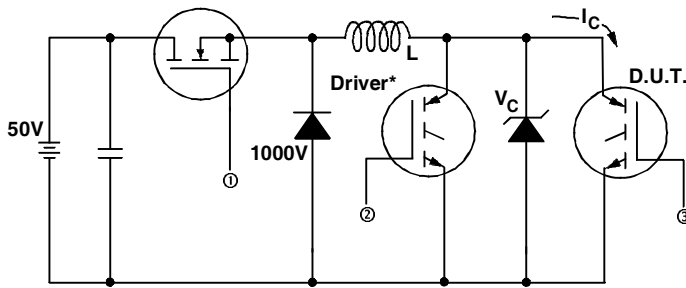
**Fig. 12** - Reverse Bias SOA



**Fig. 13a** - Clamped Inductive Load Test Circuit

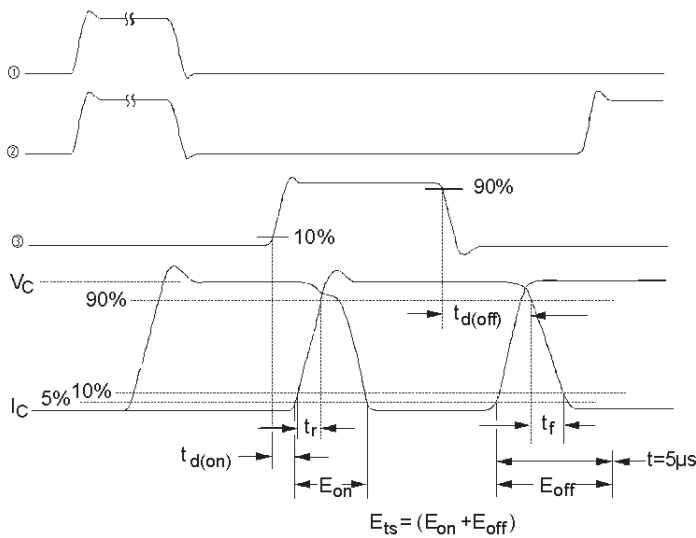


**Fig. 13b** - Pulsed Collector Current Test Circuit



**Fig. 14a** - Switching Loss Test Circuit

\* Driver same type as D.U.T., Vc = ---V

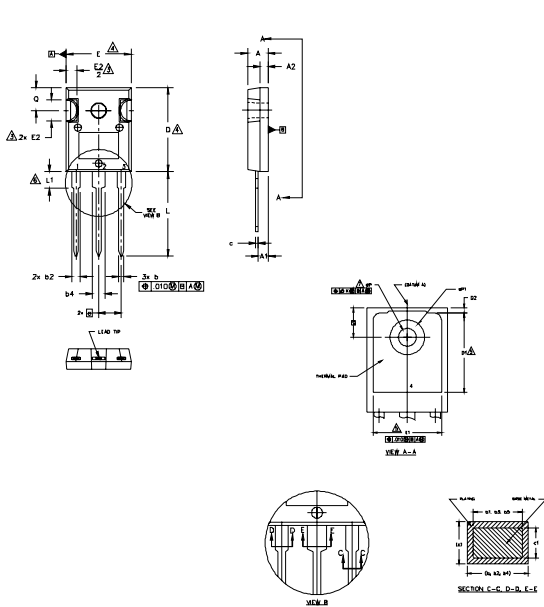


**Fig. 14b** - Switching Loss Waveforms

# IRG4PH50S-EPbF

International  
**IR** Rectifier

TO-247AD Package Outline (Dimensions are shown in millimeters (inches))



**NOTES:**

1. DIMENSIONING AND TOLERANCING AS PER ASME Y14.5M 1994.
2. DIMENSIONS ARE SHOWN IN INCHES.
- △ CONTOUR OF SLOT OPTIONAL.
- △ DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
- △ THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS D1 & E1.
- △ LEAD FINISH UNCONTROLLED IN L1.
- φP TO HAVE A MAXIMUM DRAFT ANGLE OF 1.5 ° TO THE TOP OF THE PART WITH A MAXIMUM HOLE DIAMETER OF .154 INCH.
8. OUTLINE CONFORMS TO JEDEC OUTLINE TO-247AD.

SYMBOL	DIMENSIONS				NOTES
	INCHES		MILLIMETERS		
	MIN.	MAX.	MIN.	MAX.	
A	.183	.209	4.65	5.31	
A1	.087	.102	2.21	2.59	
A2	.059	.098	1.50	2.49	
b	.039	.055	0.99	1.40	
b1	.039	.053	0.99	1.35	
b2	.065	.094	1.65	2.39	
b3	.065	.092	1.65	2.34	
b4	.102	.135	2.59	3.43	
b5	.102	.133	2.59	3.38	
c	.015	.035	0.38	0.89	
c1	.015	.033	0.38	0.84	
D	.776	.815	19.71	20.70	4
D1	.515	-	13.08	-	5
D2	.020	.053	0.51	1.35	
E	.602	.625	15.29	15.87	4
E1	.530	-	13.46	-	
E2	.178	.216	4.52	5.49	
e	.215 BSC		5.46 BSC		
ek	.010		0.25		
L	.780	.827	19.57	21.00	
L1	.146	.169	3.71	4.29	
φP	.140	.144	3.56	3.66	
φP1	-	.291	-	7.39	
Q	.209	.224	5.31	5.69	
S	.217 BSC		5.51 BSC		

**LEAD ASSIGNMENTS**

**HEXFET**

- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE
- 4.- DRAIN

**IGBTs, CoPACK**

- 1.- GATE
- 2.- COLLECTOR
- 3.- EMITTER
- 4.- COLLECTOR

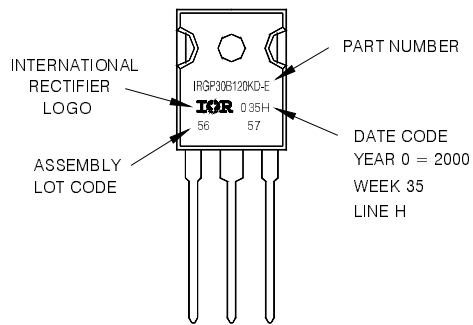
**DIODES**

- 1.- ANODE/OPEN
- 2.- CATHODE
- 3.- ANODE

## TO-247AD Part Marking Information

EXAMPLE: THIS IS AN IRGP30B120KD-E  
WITH ASSEMBLY  
LOT CODE 5657  
ASSEMBLED ON WW 35, 2000  
IN THE ASSEMBLY LINE 'H'

Note: 'P' in assembly line position  
indicates 'Lead-Free'



TO-247AD package is not recommended for Surface Mount Application.

Note: For the most current drawing please refer to IR website at: <http://www.irf.com/package/>

Data and specifications subject to change without notice.

International  
**IR** Rectifier

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